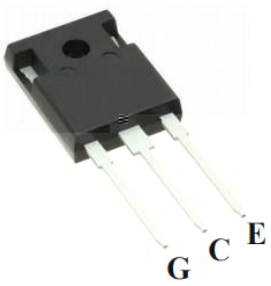
DGW60N65CTH2A



Maximum Ratings

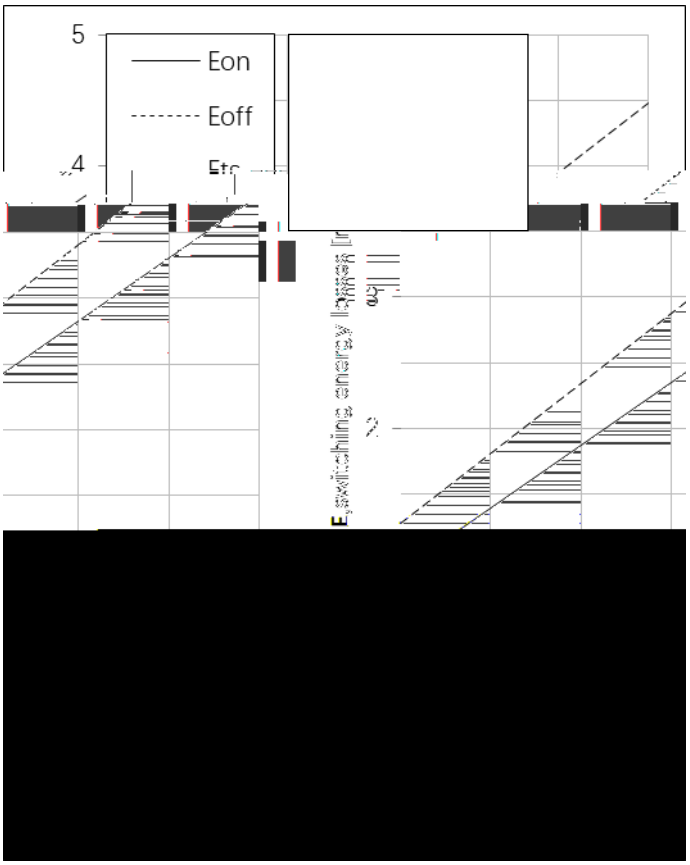
Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	650	V

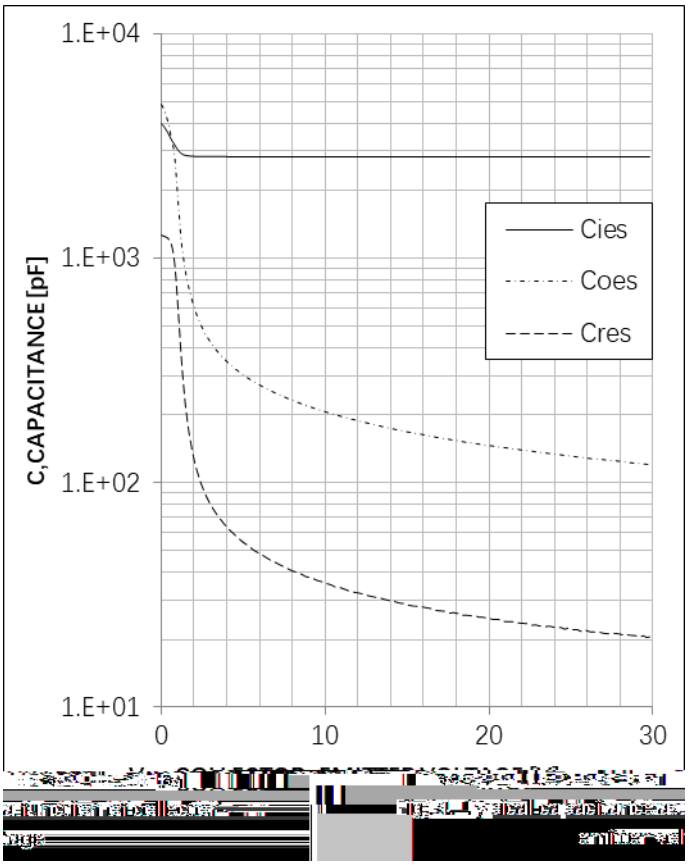
DC Collector Cur 223.39 -14( )] 41 0 0 1 101.35

Electrical Characteristics of the Diode ÄTj= 25

Electrical Characteristics of the DIODE

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit





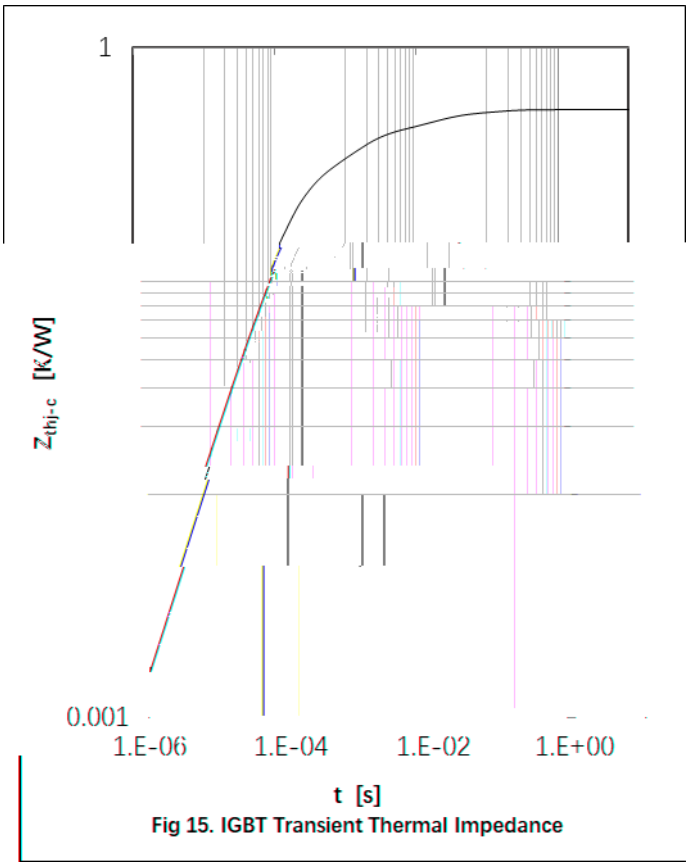
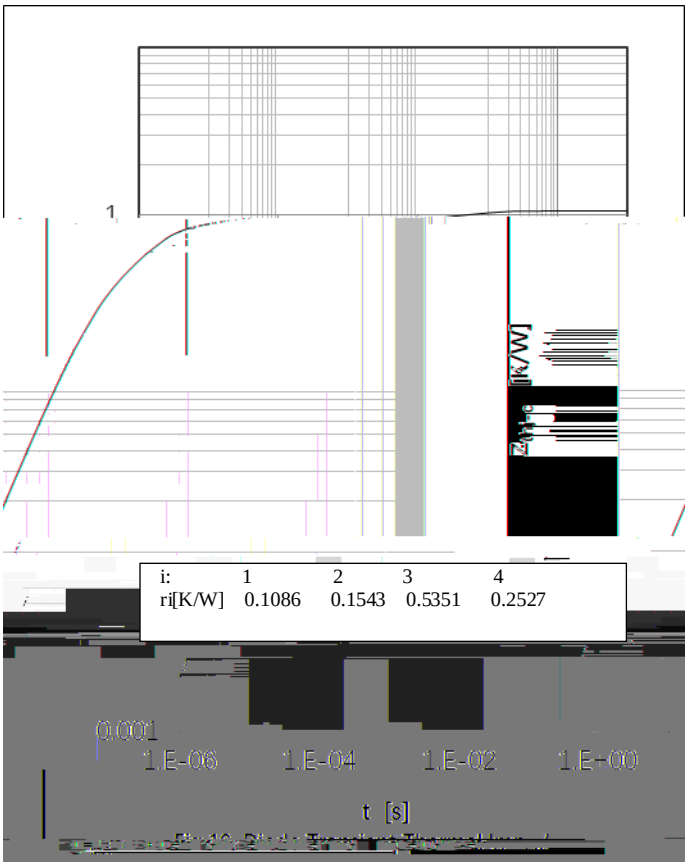
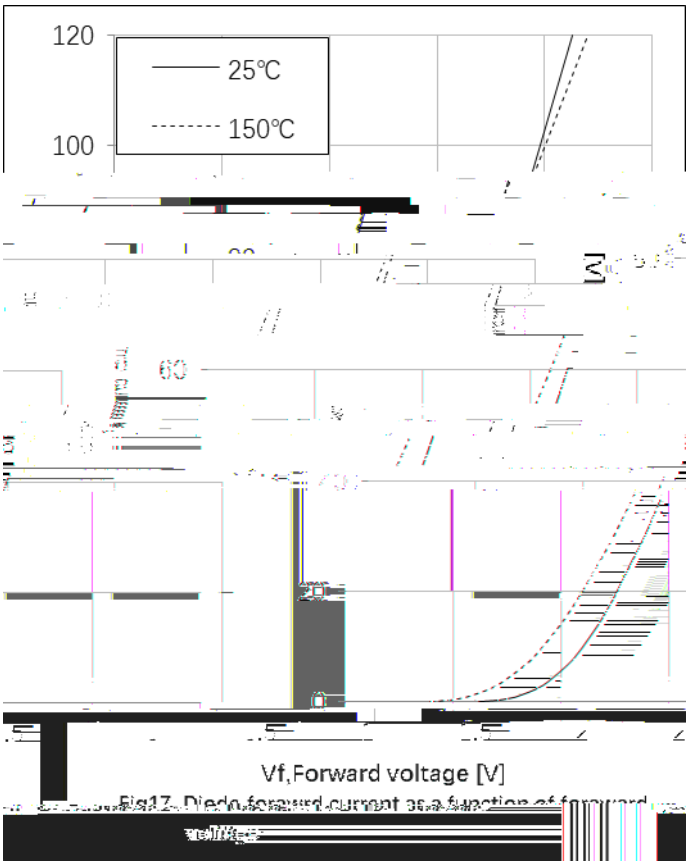
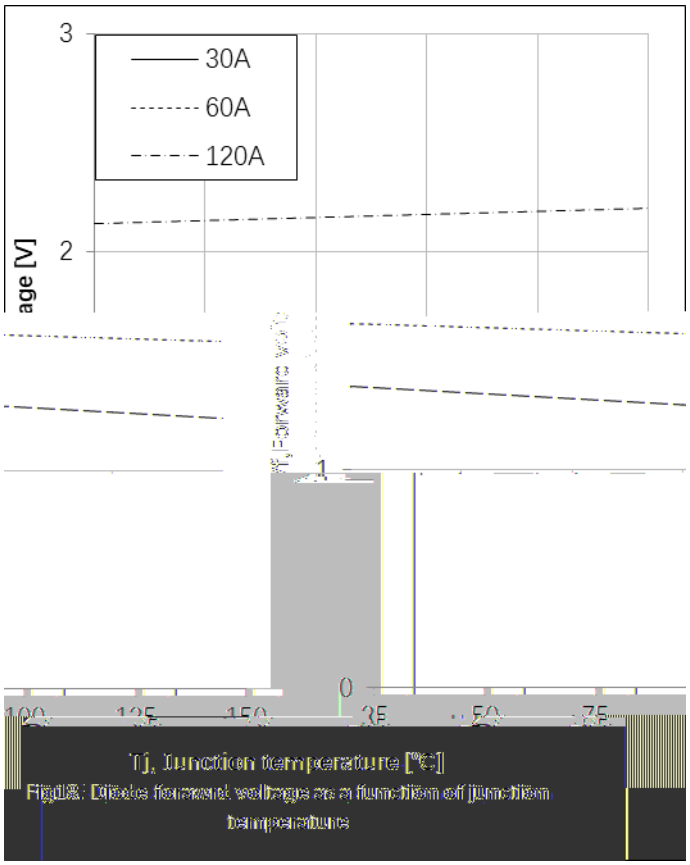
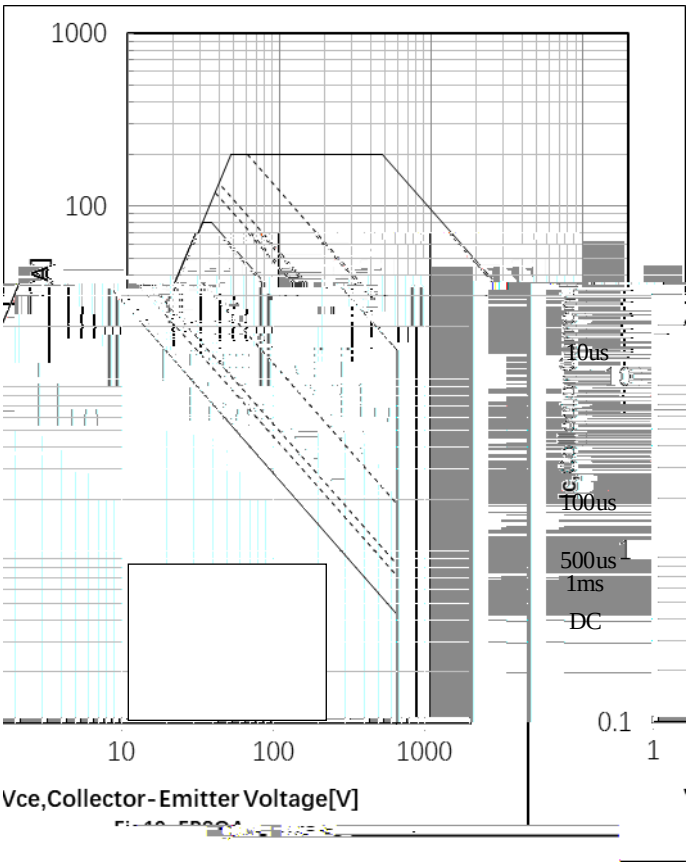


Fig 15. IGBT Transient Thermal Impedance

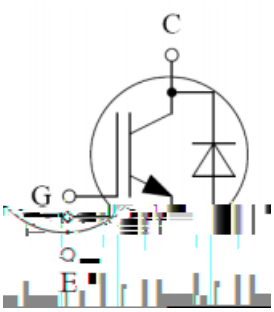



120
100
25℃
150℃
60
Vf,Forward voltage [V]


3
2
1
0
30A
60A
120A
age [V]
Tj, Junction temperature [℃]


1000
100
10us
100us
500us
1ms
DC
0.1
1
10
100
1000
Vce,Collector-Emitter Voltage[V]

D D



Package Outline Information

TO-247AB		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.0	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.70	21.30
D1	16.25	16.85

D